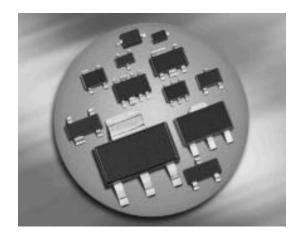


Silicon Variable Capacitance Diodes

- Frequency range up to 2 GHz
- Special design for use in TV-sat tuners
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





BB831



Туре	Package	Configuration	L S(nH)	Marking
BB831	SOD323	single	1.8	white T

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_{R}	30	V
Peak reverse voltage	V_{RM}	35	
$(R \ge 5k\Omega)$			
Forward current	l _F	20	mA
Operating temperature range	T_{op}	-55 12 5	°C
Storage temperature	$T_{ m stg}$	-55 150	

¹Pb-containing package may be available upon special request



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

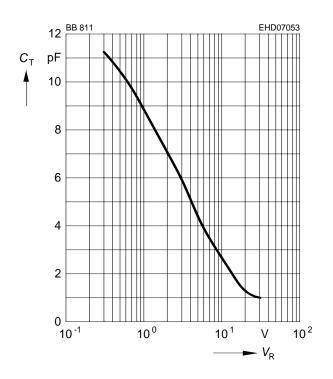
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_{R}				nA
<i>V</i> _R = 30 V			-	20	
$V_{R} = 30 \text{ V}, \ T_{A} = 85 \text{ °C}$		-	-	500	
AC Characteristics					
Diode capacitance	C_{T}				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		7.8	8.8	9.8	
$V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$		0.85	1.02	1.2	
Capacitance ratio	C _{T1} /C _{T28}	7.8	8.6	9.5	
$V_{R} = 1 \text{ V}, V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching ¹⁾	$\Delta C_{T}/C_{T}$	-	-	3	%
$V_{R} = 1 \text{ V}, V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	r _S	-	1	-	Ω
$V_{R} = 1 \text{ V}, f = 100 \text{ MHz}$					

¹For details please refer to Application Note 047.

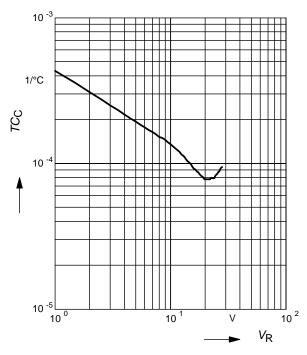


Diode capacitance $C_T = f(V_R)$

f = 1MHz



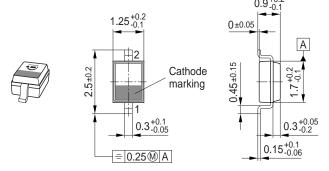
Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



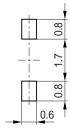
3 2007-04-20



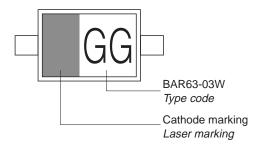
Package Outline



Foot Print

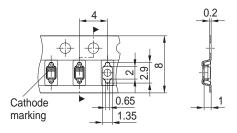


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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